

Call for Papers

Special Section on Fundamentals and Applications of Advanced Semiconductor Devices

The IEICE (Institute of Electronics, Information and Communication Engineers) Transactions on Electronics announce a Special Section on "Fundamentals and Applications of Advanced Semiconductor Devices" to be published in **May 2009**. As digital processing units penetrate deeply into information society, the demand for high-performance semiconductor devices is kept growing. The purpose of this Special Section is to discuss various aspects of advanced semiconductor devices from fundamental physics to circuit applications. These include Si-based MOSFETs and bipolar transistors, compound semiconductor devices, and nano-scale devices.

1. Scope

Contributions are solicited in the following areas (but are not limited to these areas):

- *Advanced integration technology
- *ULSI process
- *High speed devices and circuits
- *High power devices
- *Wide bandgap materials and devices
- *Novel devices and circuits
- *MOSFET and bipolar (hetero) junction transistors
- *Compound semiconductor materials and devices
- *Microwave/Millimeter-wave devices and circuits
- *Materials, devices and application of TFTs
- *Quantum effect/Single electron devices
- *Characterization and simulation

2. Submission Instructions

The deadline for submission is **August 25, 2008**. This special section will accept only papers by electronic submission. Prospective authors are requested to follow the submission procedure described below.

- (1) Submit a paper using the IEICE Web site https://review.ieice.org/regist_e.aspx. Authors should choose the [Special-EC] Fundamentals and Applications of Advanced Semiconductor Devices as a "Type of Issue (Section)/Category of Transactions" on the online screen. Do not choose [Regular-EC].
- (2) Send "One copy of the printed manuscript including figures and tables", "Copyright Transfer and Page Charge Agreement" and "Confirmation Sheet of Manuscript Registration" to

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by postal mail. (NOT by FAX or E-mail). Please do not forget to send "Copyright Transfer and Page Charge Agreement" and "Confirmation Sheet of Manuscript Registration". We will not start the review process without them, even if we receive the manuscript.

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*Please note that if accepted, all authors, including authors of invited papers, should pay for the page charges covering partial cost of publication. Authors will receive 50 copies of the reprint.

*At least one of the authors must be an IEICE member when the manuscript is submitted for review. Invited papers are an exception. We recommend that authors unaffiliated with IEICE apply for membership. For membership applications, please visit the web-page, <http://www.ieice.org/eng/member/OM-appli.html>.